

ABSTRACT

1 SEMICONDUCTOR DEVICE WITH BURIED ELECTRODE

A semiconductor device including a bipolar transistor, has a collector region including a first semiconductor region of the first electroconduction type and a second semiconductor region of the first electroconduction type having higher resistance than the first semiconductor region, a base region including a semiconductor region of the second electroconduction type, and an emitter region including a semiconductor region of the first electroconduction type. The semiconductor device further comprises a metal layer region for connecting the first semiconductor region and the collector electrode on the collector region provided within the second semiconductor region layer of the collector region.

20

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